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Correction: Raw product of rare-earth ore works as a high-*k* gate insulator for low-voltage operable organic field-effect transistors

 Xue-feng She,^{ab} Jingsong Wang,^a Qingguo Xue^a and Wentao Xu^{*bc}

 Correction for 'Raw product of rare-earth ore works as a high-*k* gate insulator for low-voltage operable organic field-effect transistors' by Xue-feng She *et al.*, *RSC Adv.*, 2016, 6, 114593–114598.

The structure of the cyanoethylated pullulan polymer depicted in Fig. 1 was incorrect and the correct structure of the polymer unit is represented below:

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

^aState Key Laboratory of Advanced Metallurgy, University of Science and Technology Beijing (USTB), Beijing 100083, China

^bDepartment of Materials Science and Engineering, Pohang University of Science and Technology (POSTECH), 77 Cheongam-ro, Nam-gu, Pohang, Gyungbuk 790-784, Republic of Korea. E-mail: wentao@postech.ac.kr

^cDepartment of Chemical Engineering, Stanford University, Stanford, CA 94305, USA